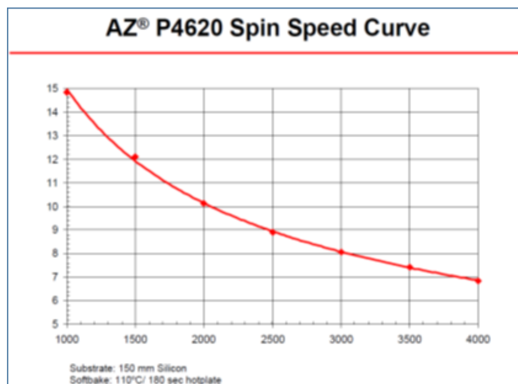
AZ P4620 Photoresist

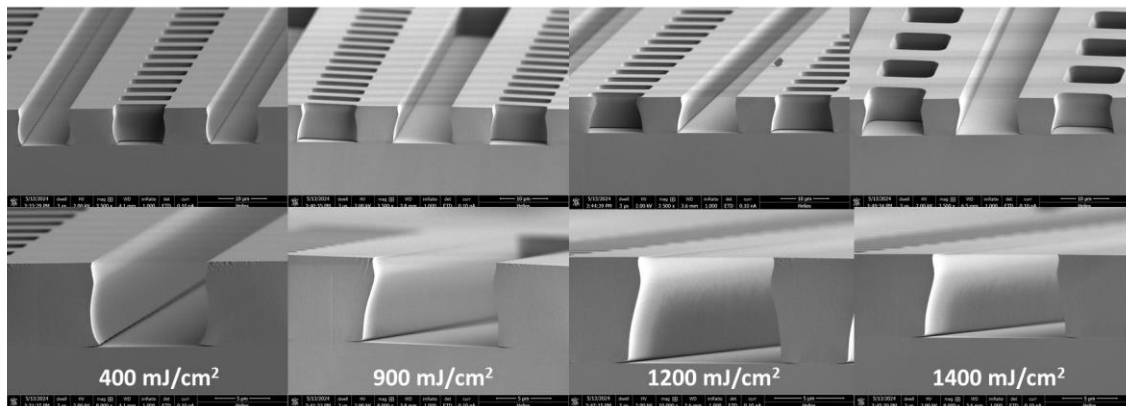
- **The AZ P4620 is a positive photoresist for a thick RIE etch mask and a lift off of Au or Cu plating.**
- **Exposure with g-line (λ = 465nm) or h-line (405nm) is recommended.**

- **Process with Heidelberg MLA**
  - λ = 375nm
  - Spin coating: 2000 - 4000 rpm
  - Soft bake: 100 - 110°C for 3 min.
  - Exposure (mJ/cm^2): 400 – 1400
  - Development: AZ 400K (1:4) for 4 min.
  - Thickness: note that the thickness measured is different from the chart.
    - 4 µm at 4000 rpm
    - 8 µm at 2000 rpm



- **Side wall profile with 10 µm lines and squares**

Spin @ 2000 rpm |thickness: 8µm| SB: 100°C • 3min | AZ 400K(1:4) • 4 min



Spin @ 4000 rpm | thickness: 4µm | SB: 110°C • 3min | AZ 400K(1:4) • 4 min